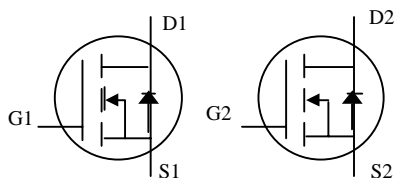
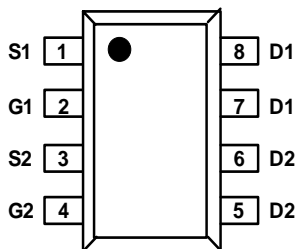


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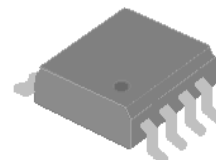
20V-N 沟道增强型双MOS管

 $R_{DS(ON)}, V_{GS}@2.5V, I_{DS}@5.0A = 42m\Omega (MAX)$
 $R_{DS(ON)}, V_{GS}@4.5V, I_{DS}@6.0A = 30m\Omega (MAX)$


内部示意图



管脚说明



SO-8 实物图 (顶层)

绝对最大额定值 ($T_A=25^{\circ}C$, 除非另有注明)

参数	符号	最大值	单位
漏源极电压	V_{DS}	20	V
栅源极电压	V_{GS}	± 12	V
连续漏电流	I_D	$T_A=25^{\circ}C$	6
		$T_A=70^{\circ}C$	4.2
脉冲漏电流	I_{DM}	20	A
功耗	P_D	$T_A=25^{\circ}C$	2
		$T_A=70^{\circ}C$	1.28
温度范围	T_J, T_{STG}	-55~150	$^{\circ}C$

热特性

参数	符号	典型值	最大值	单位
最大管结温度	$R_{\theta JA}$	56	62.5	$^{\circ}C/W$
最大管结温度				
最大热阻	$R_{\theta JL}$	40	48	$^{\circ}C/W$

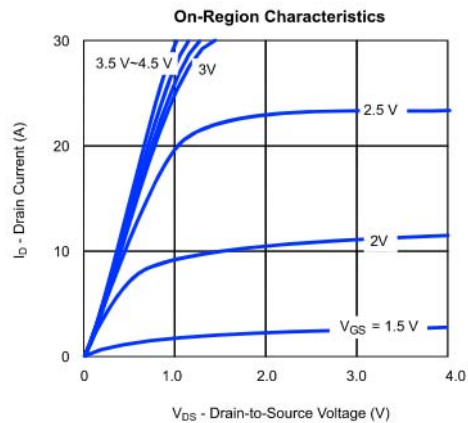
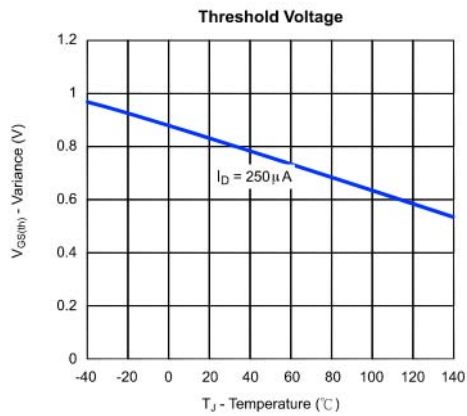
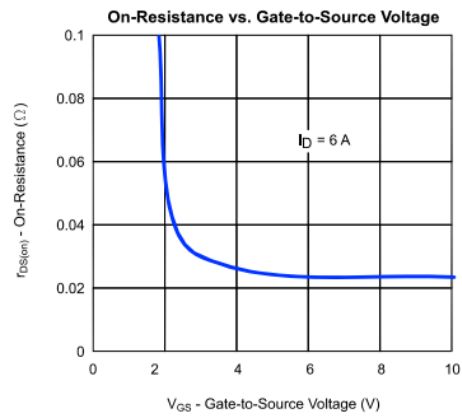
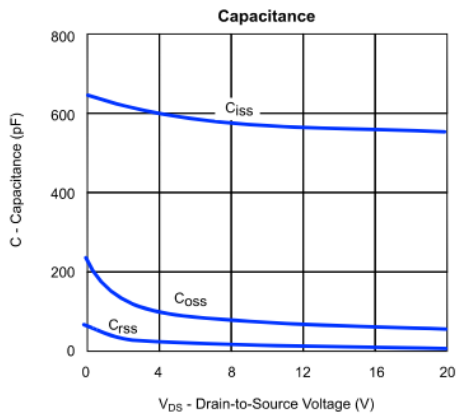
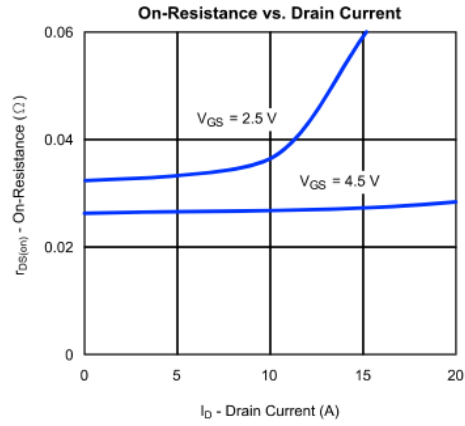
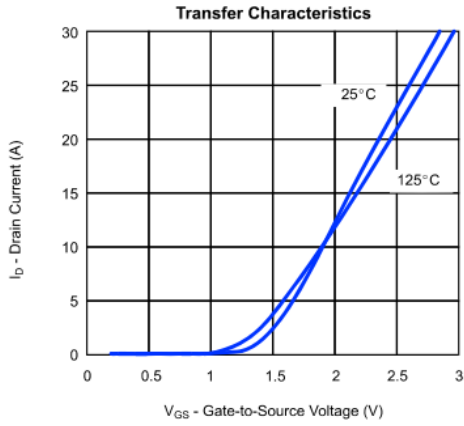
电特性

(T_J=25℃, 除非另有注明)

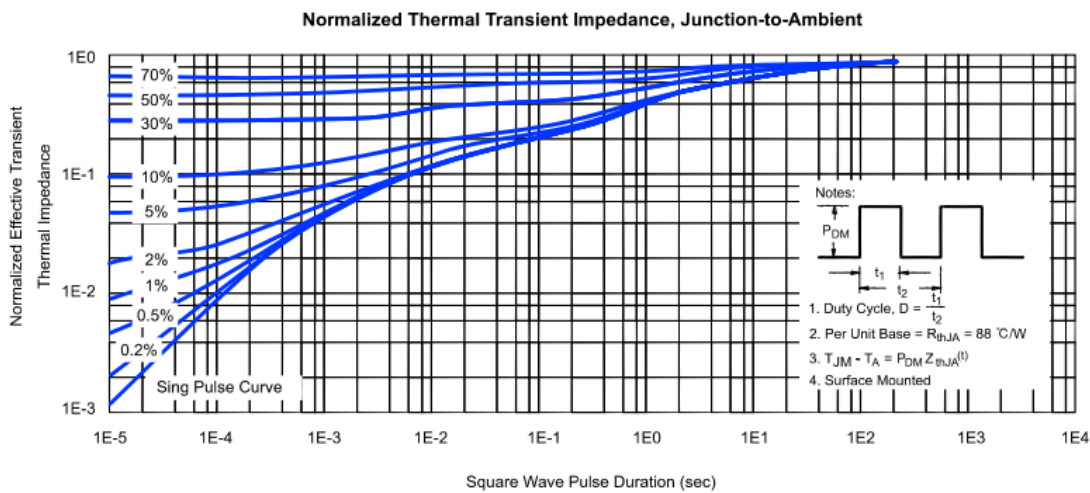
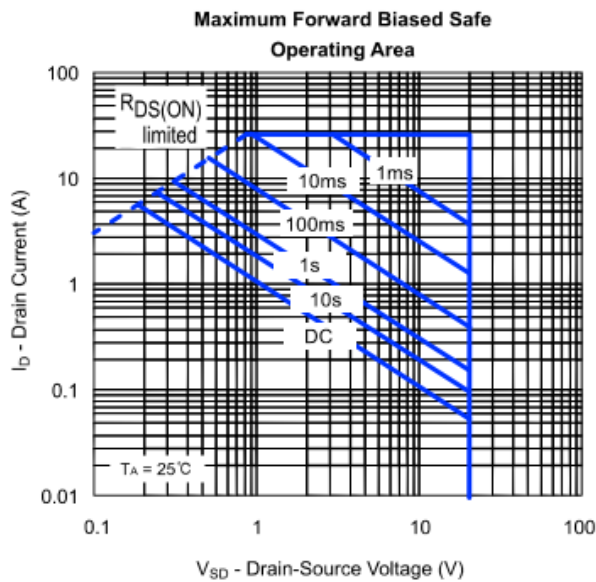
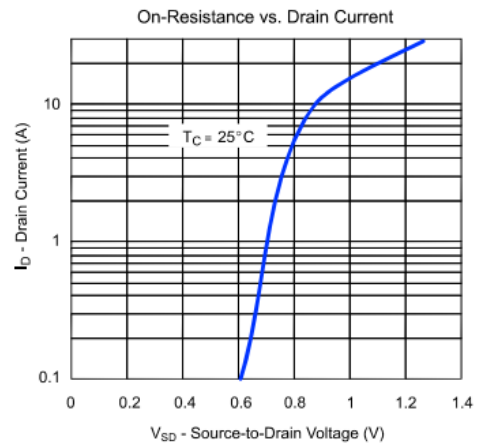
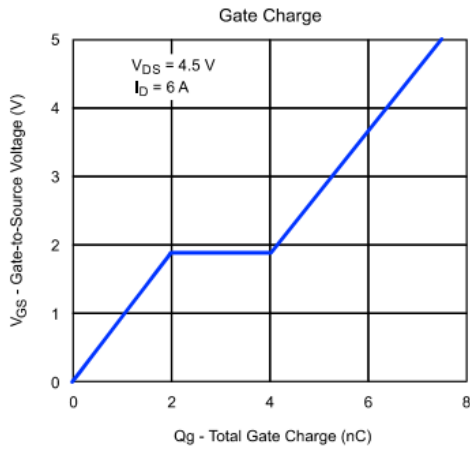
参数	符号	测试条件	最小	典型	最大	单位
静态部分						
漏源击穿电压	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	20			V
Drain-source 导通内阻	R _{DS(ON)}	V _{GS} = 4.5V, I _{DS} = 6A		21	30	mΩ
Drain-source 导通内阻	R _{DS(ON)}	V _{GS} = 2.5V, I _{DS} = 5A		26	42	mΩ
栅极阈值电压	V _{GS(th)}	V _{GS} = V _{GS} , I _D = 250uA	0.5	0.75	1	V
漏源极漏电流	I _{DSS}	V _{DSS} = 20V, V _{GS} = 0V			1	uA
栅源极漏电流	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V			±100	nA
动态部分						
栅极总电荷	Q _G	V _{DS} = 10V, I _D = 6A V _{GS} = 4.5V		6.24	8.11	nC
栅源电荷	Q _{GS}			1.64	2.13	
栅漏电荷	Q _{GB}			1.34	1.74	
开始延迟时间	T _{d(on)}	V _{DD} = 10V, I _D = 6A I _D = 1A, V _{GS} = 4.5V		10.4	20.8	ns
上升时间	T _r			4.4	8.8	
关闭延迟时间	T _{d(off)}			27.36	54.72	
下降时间	T _f			4.16	8.32	
输入电容	C _{iss}	V _{DS} = 8V, V _{GS} = 0V f = 1.0MHz		522.3		pF
输出电容	C _{oss}			98.48		
反向传输电容	C _{rss}			74.69		
源漏极二极管						
二极管最大正向电流	I _S				1.7	A
二极管正向电压	V _{SD}	I _S = 1.7A, V _{GS} = 0V		0.74		V

曲线图

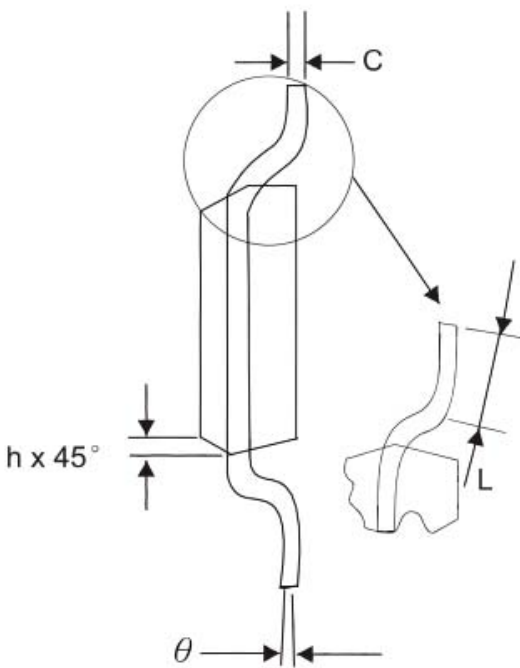
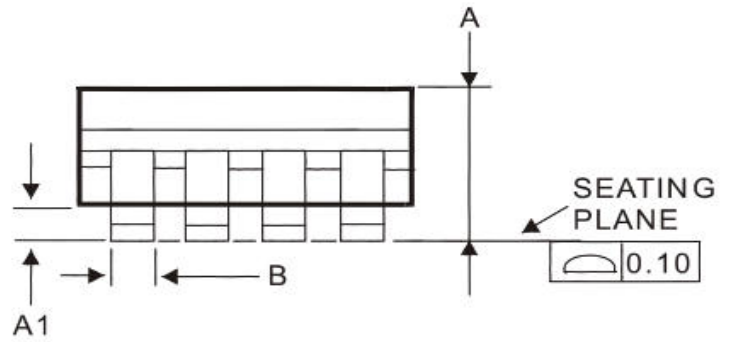
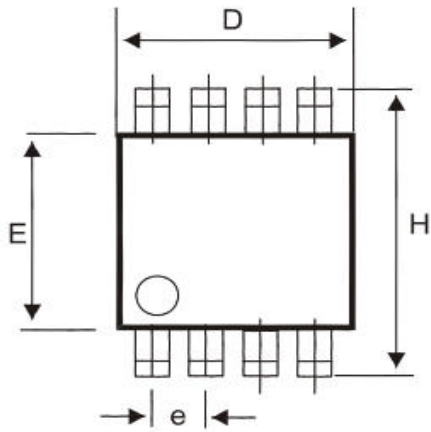
Typical Characteristics (T_J = 25°C Noted)



Typical Characteristics (T_J = 25°C Noted)



封装信息：SO-8



DIM	MILLIMETERS	
	MIN	MAX
A	1.35	1.75
A1	0.10	0.25
B	0.35	0.49
C	0.18	0.25
D	4.80	5.00
E	3.80	4.00
e	1.27 BSC	
H	5.80	6.20
h	0.25	0.50
L	0.40	1.25
θ	0°	7°